Agnes Gubicza

List of Publications by Year
in descending order

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11 papers	183 citations	1306789 7 h-index	1372195 10 g-index

11 all docs	11 docs citations	11 times ranked	284 citing authors

#	Article	IF	Citations
1	Conductive Hybrid Cuâ€HHTPâ€TCNQ Metalâ€“Organic Frameworks for Chemiresistive Sensing. Advanced Electronic Materials, 2022, 8, 2100871.	2.6	5
2	A non-oxidizing fabrication method for lithographic break junctions of sensitive metals. Nanoscale Advances, 2020, 2, 3829-3833.	2.2	0
3	Nanosecond resistive switching in Ag/AgI/PtIr nanojunctions. Beilstein Journal of Nanotechnology, 2020, 11, 92-100.	1.5	7
4	Quantum Interference Enhanced Chemical Responsivity in Singleâ€Molecule Dithienoborepin Junctions. Chemistry - A European Journal, 2019, 25, 15141-15146.	1.7	18
5	Universal 1/f type current noise of Ag filaments in redox-based memristive nanojunctions. Nanoscale, 2019, 11, 4719-4725.	2.8	19
6	Exploiting supramolecular assemblies for filterless ultra-narrowband organic photodetectors with inkjet fabrication capability. Journal of Materials Chemistry C, 2019, 7, 14639-14650.	2.7	24
7	In situ impedance matching in Nb/Nb₂O₅/PtIr memristive nanojunctions for ultra-fast neuromorphic operation. Nanoscale, 2018, 10, 19290-19296.	2.8	6
8	Asymmetry-induced resistive switching in Ag-Ag2S-Ag memristors enabling a simplified atomic-scale memory design. Scientific Reports, 2016, 6, 30775.	1.6	30
9	Resistive switching in metallic Ag₂S memristors due to a local overheating induced phase transition. Nanoscale, 2015, 7, 11248-11254.	2.8	19
10	Non-exponential resistive switching in Ag₂S memristors: a key to nanometer-scale non-volatile memory devices. Nanoscale, 2015, 7, 4394-4399.	2.8	32
11	A fast operation of nanometer-scale metallic memristors: highly transparent conductance channels in Ag₂S devices. Nanoscale, 2014, 6, 2613-2617.	2.8	23